

# NCE N-Channel Enhancement Mode Power MOSFET

### Description

The NCE2025I uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

## **General Features**

- V<sub>DS</sub> =20V,I<sub>D</sub> =25A
  R<sub>DS(ON)</sub> <13mΩ @ V<sub>GS</sub>=10V (Typ:10.5mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

## Application

- Power switching application
- Load switching
- Uninterruptible power supply

### 100% UIS TESTED!

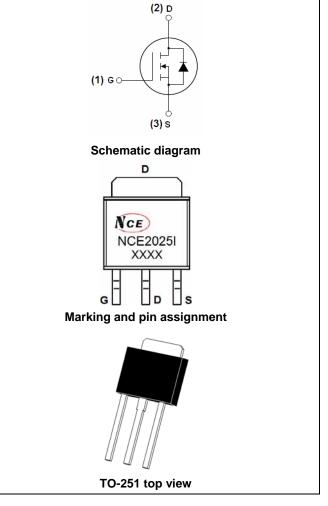
### 100% ΔVds TESTED!

# Package Marking and Ordering Information

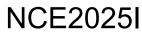
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE2025I	NCE2025I	TO-251	-	-	-

### Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	VDS	20	V	
Gate-Source Voltage	Vgs	±12	V	
Drain Current-Continuous	I <sub>D</sub>	25	А	
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	17.5	А	
Pulsed Drain Current	I <sub>DM</sub>	75	А	
Maximum Power Dissipation	PD	40	W	
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	150	mJ	
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175	°C	
Thermal Characteristic		·		
Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	3.8	°C/W	







# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•	•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	20	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)			•	•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	10.5	13	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =20A	10	-	-	S
Dynamic Characteristics (Note4)			•	•		
Input Capacitance	C <sub>lss</sub>			900		PF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V, F=1.0MHz		162		PF
Reverse Transfer Capacitance	C <sub>rss</sub>			105		PF
Switching Characteristics (Note 4)			•	•		
Turn-on Delay Time	t <sub>d(on)</sub>		-	4.5	-	nS
Turn-on Rise Time	tr	VGS=10V,VDS=10V	-	9.2	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	RL=0. 5Ω,RGEN=3Ω	-	18.7	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3.3	-	nS
Total Gate Charge	Qg			15		nC
Gate-Source Charge	Q <sub>gs</sub>	VGS=10V,VDS=10V,ID=20A		1.8		nC
Gate-Drain Charge	Q <sub>gd</sub>			2.8		nC
Drain-Source Diode Characteristics			•	•		
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =25A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>	-	-	-	25	А
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 20A	-	18	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	9.5	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

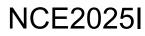
4. Guaranteed by design, not subject to production

5. EAS condition: Tj=25  $^\circ C$  ,V\_DD=10V,V\_G=10V,L=0.5mH,Rg=25\Omega



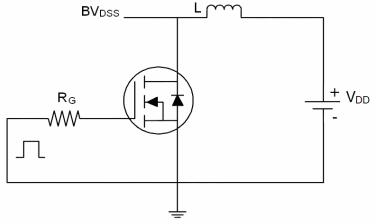
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Pb Free Product

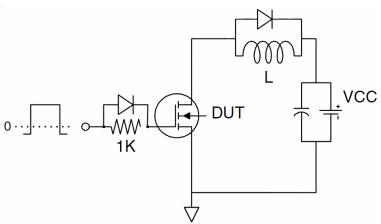


# Test circuit

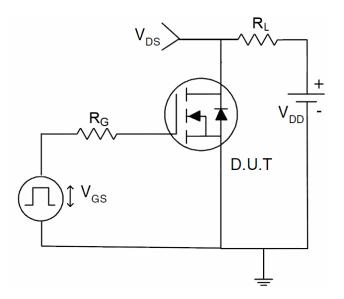
1) E<sub>AS</sub> test Circuits



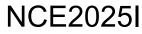
# 2) Gate charge test Circuit:



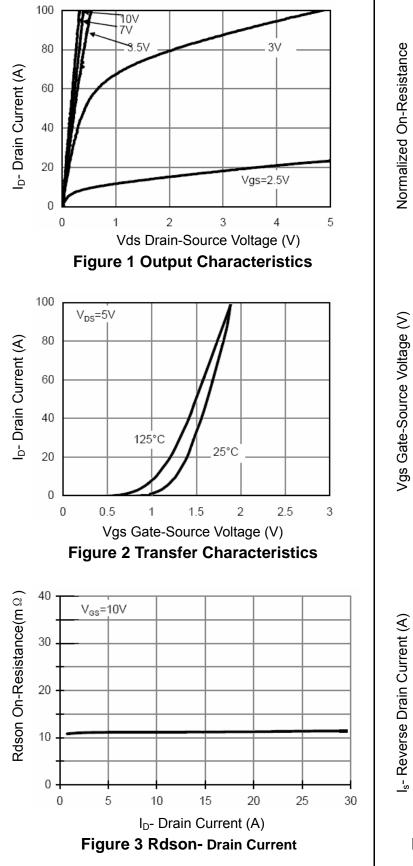
3) Switch Time Test Circuit:







# **Typical Electrical and Thermal Characteristics (Curves)**



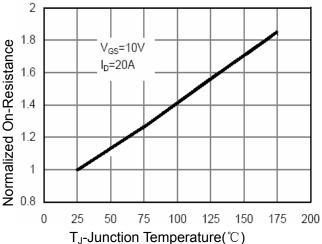
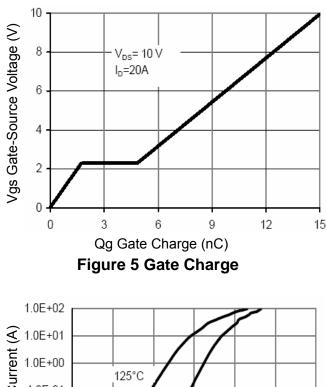


Figure 4 Rdson-Junction Temperature



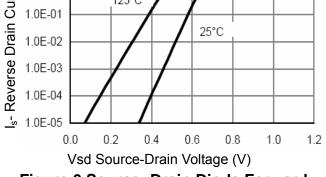


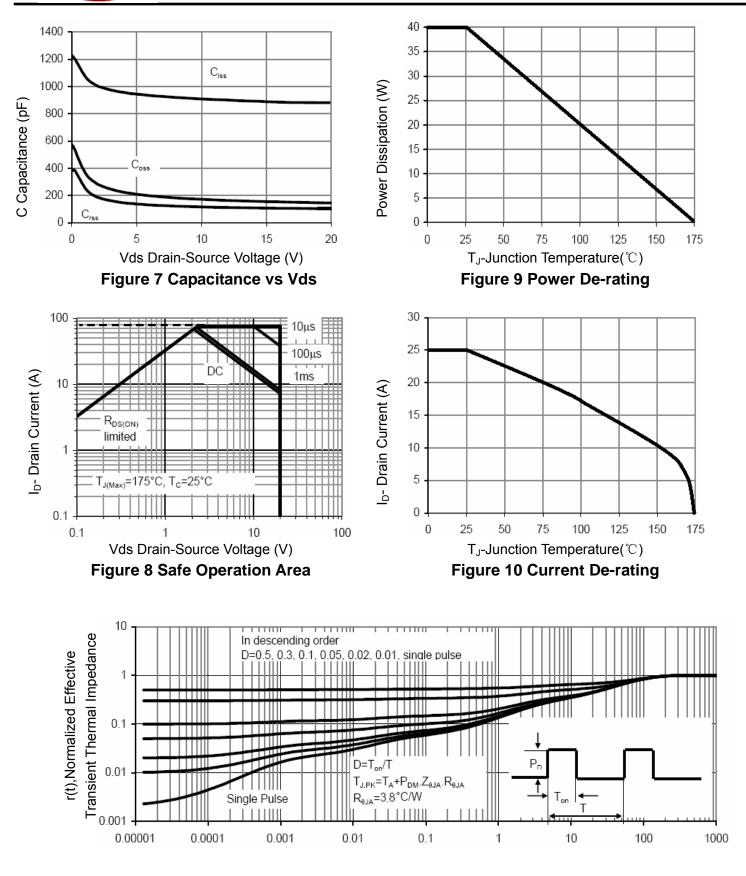
Figure 6 Source- Drain Diode Forward



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NCE2025I

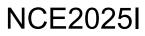


Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance

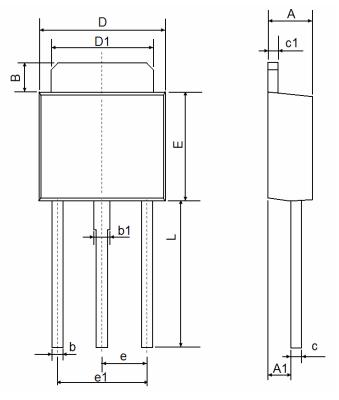


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# **TO-251 Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	1.050	1.350	0.042	0.054	
В	1.350	1.650	0.053	0.065	
b	0.500	0.700	0.020	0.028	
b1	0.700	0.900	0.028	0.035	
С	0.430	0.580	0.017	0.023	
c1	0.430	0.580	0.017	0.023	
D	6.350	6.650	0.250	0.262	
D1	5.200	5.400	0.205	0.213	
E	5.400	5.700	0.213	0.224	
е	2.300 TYP.		0.091 TYP.		
e1	4.500	4.700	0.177	0.185	
L	7.500	7.900	0.295	0.311	

#### Notes

1. All dimensions are in millimeters.

2. Tolerance ±0.10mm (4 mil) unless otherwise specified

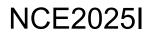
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.

4. Dimension L is measured in gauge plane.

5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exac







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